

Localized states and electronic excitation mobility in solids with short order fluctuation of crystal structure

Andrei Belsky

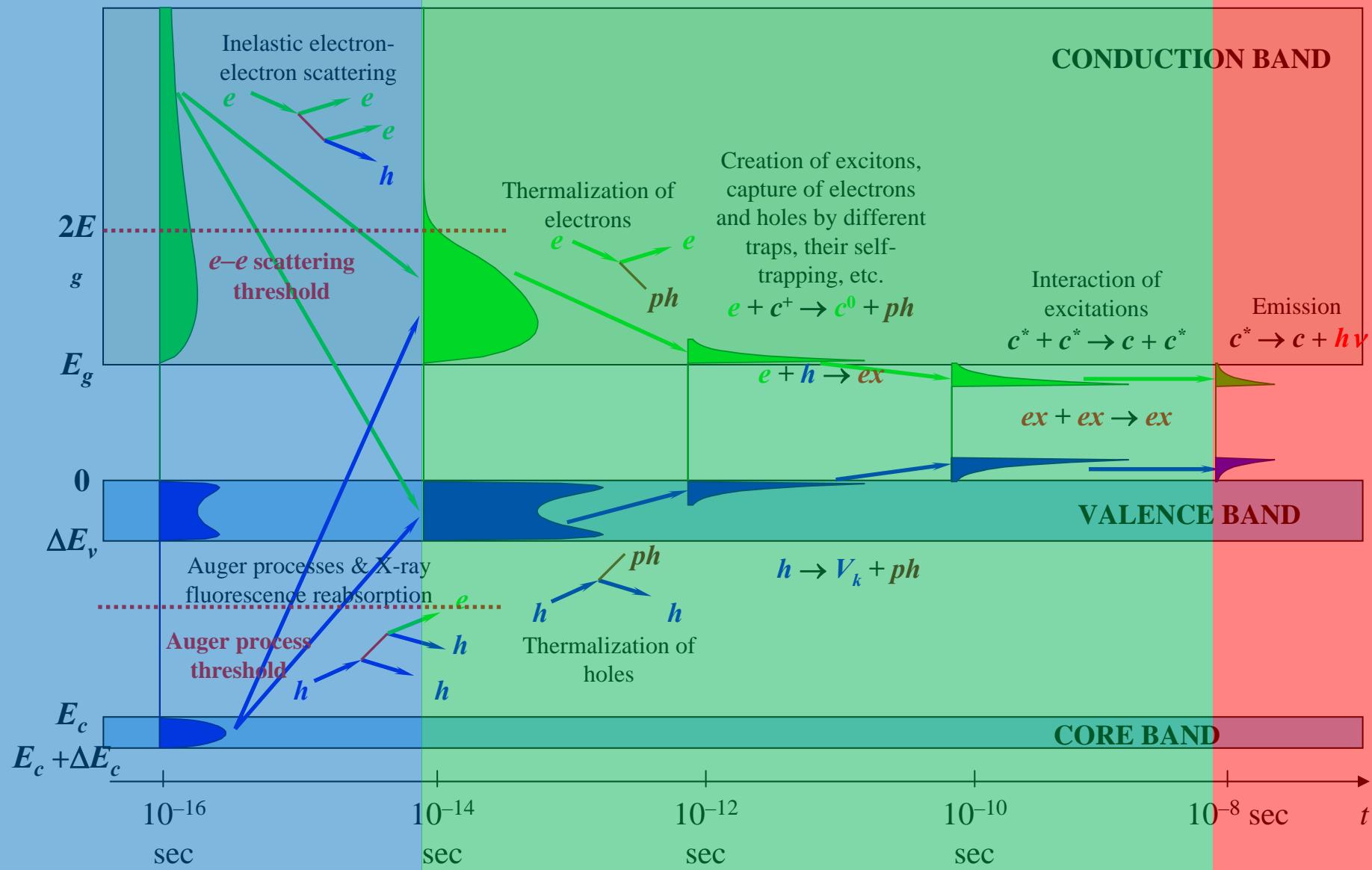
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- Experimental study of relaxation dynamics:
 - Decay kinetics under VUV excitation and elementary processes in scintillators
- Spatial scales for processes in scintillators:
 - Solid solutions of scintillators

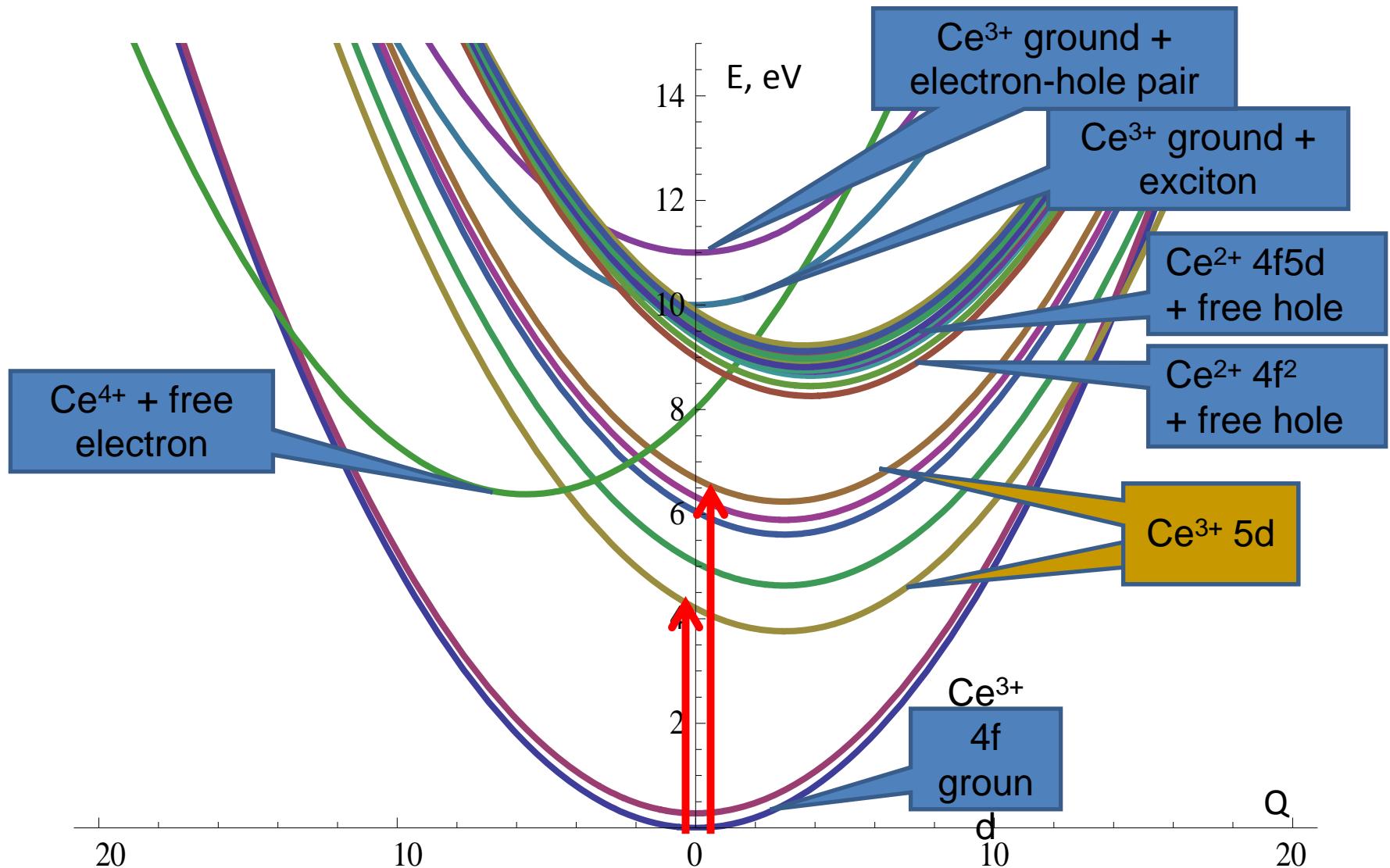
Cascade

Transport

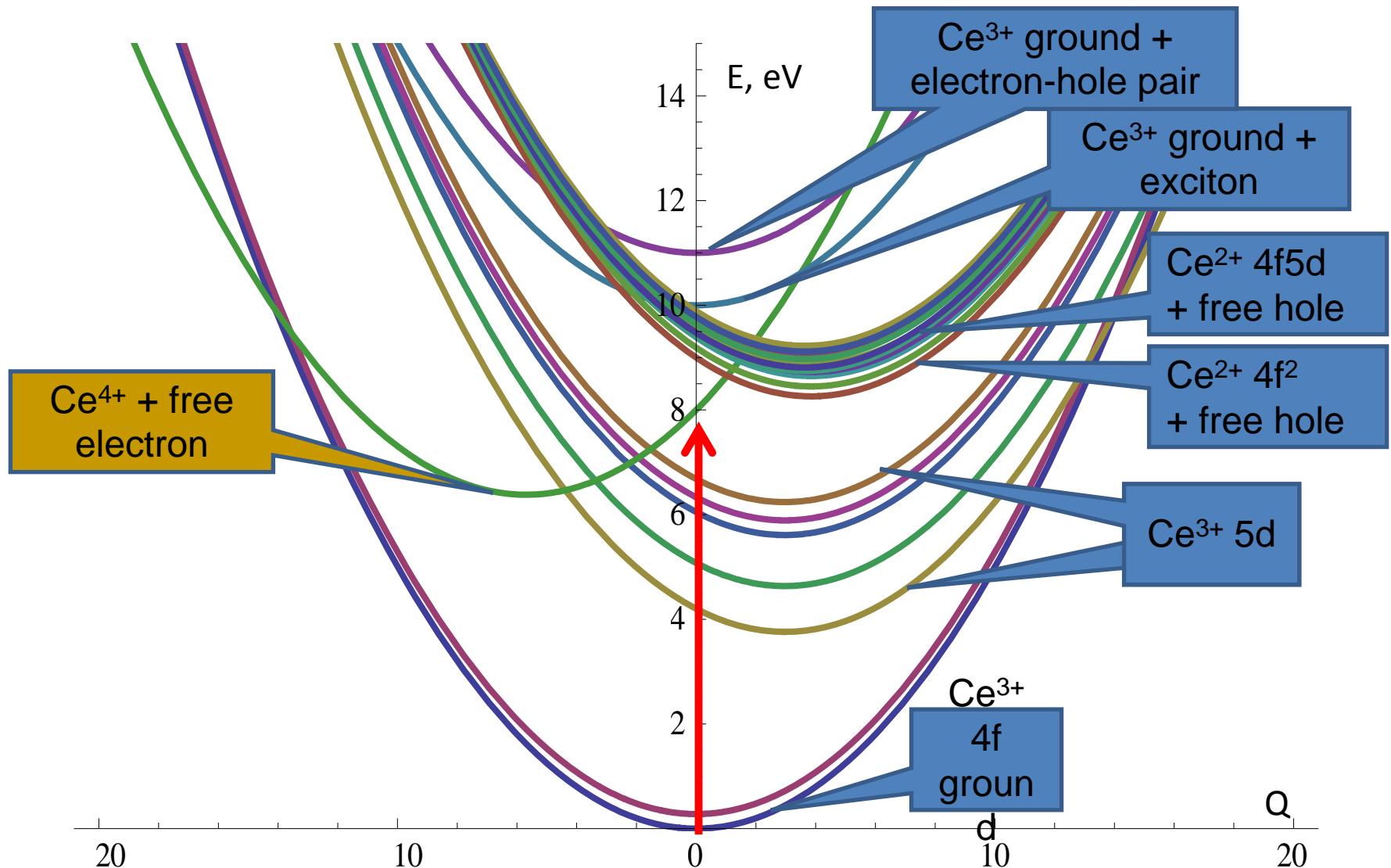
Center



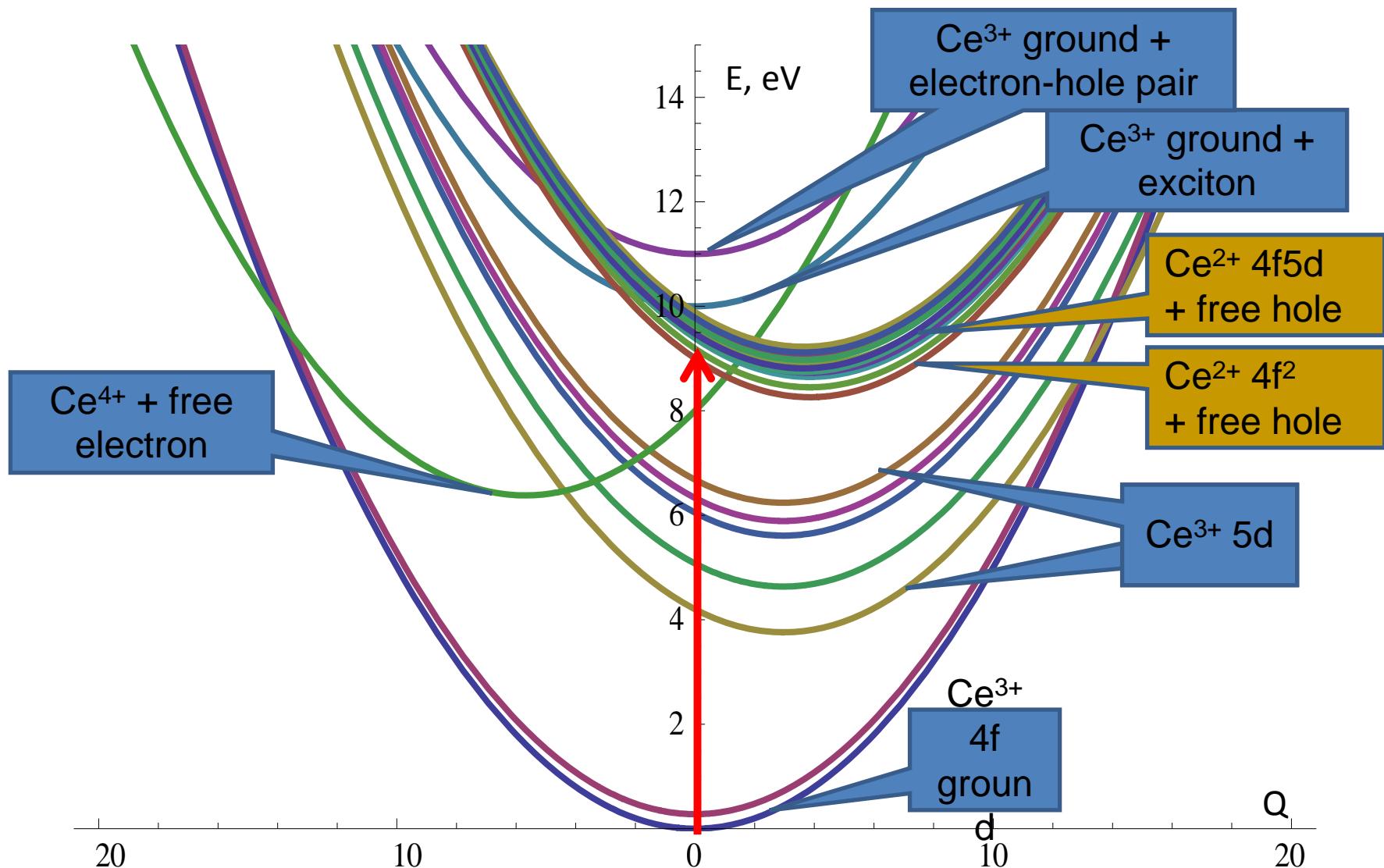
Excitation & ionization of Ce^{3+}



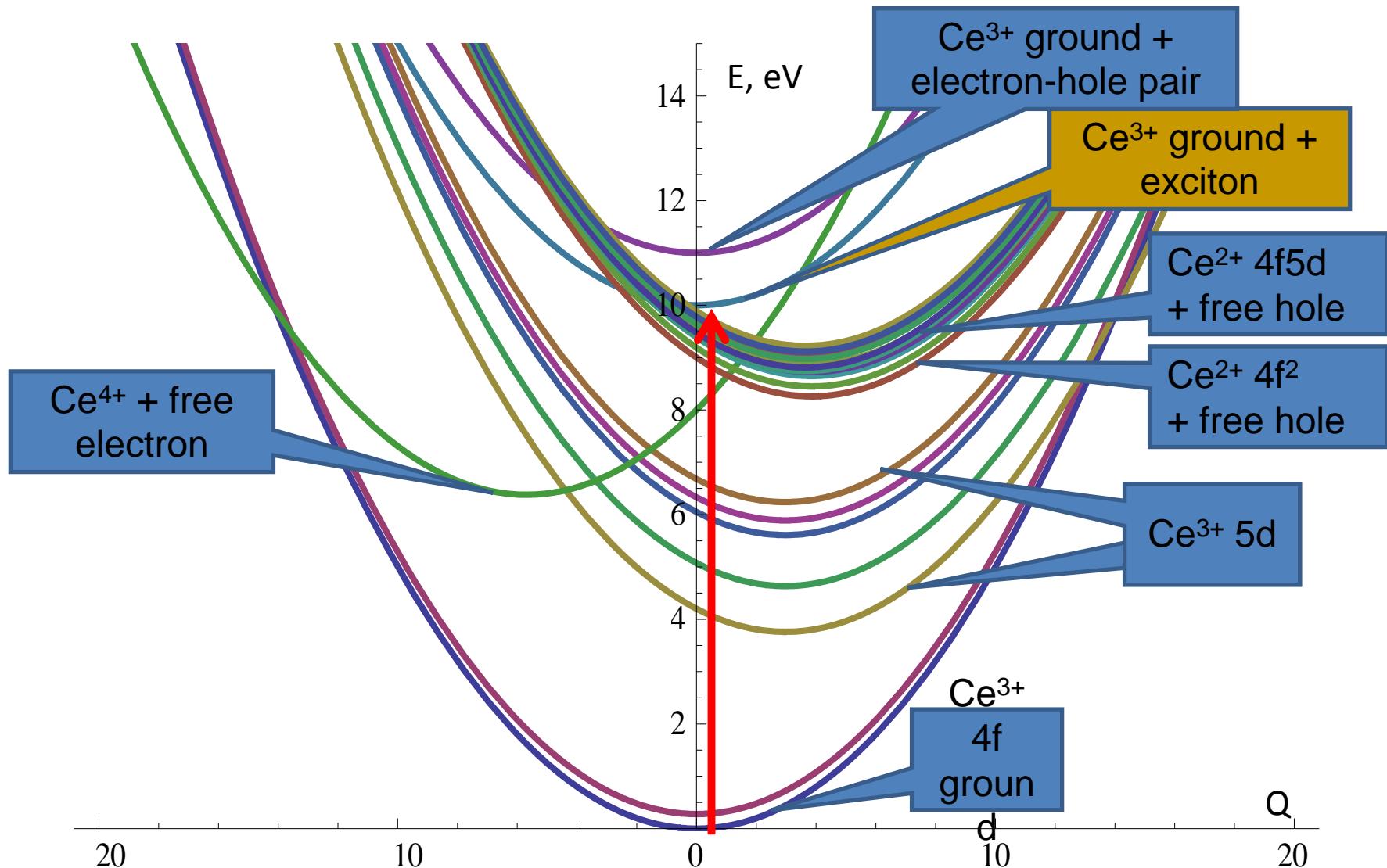
Excitation & ionization of Ce^{3+}



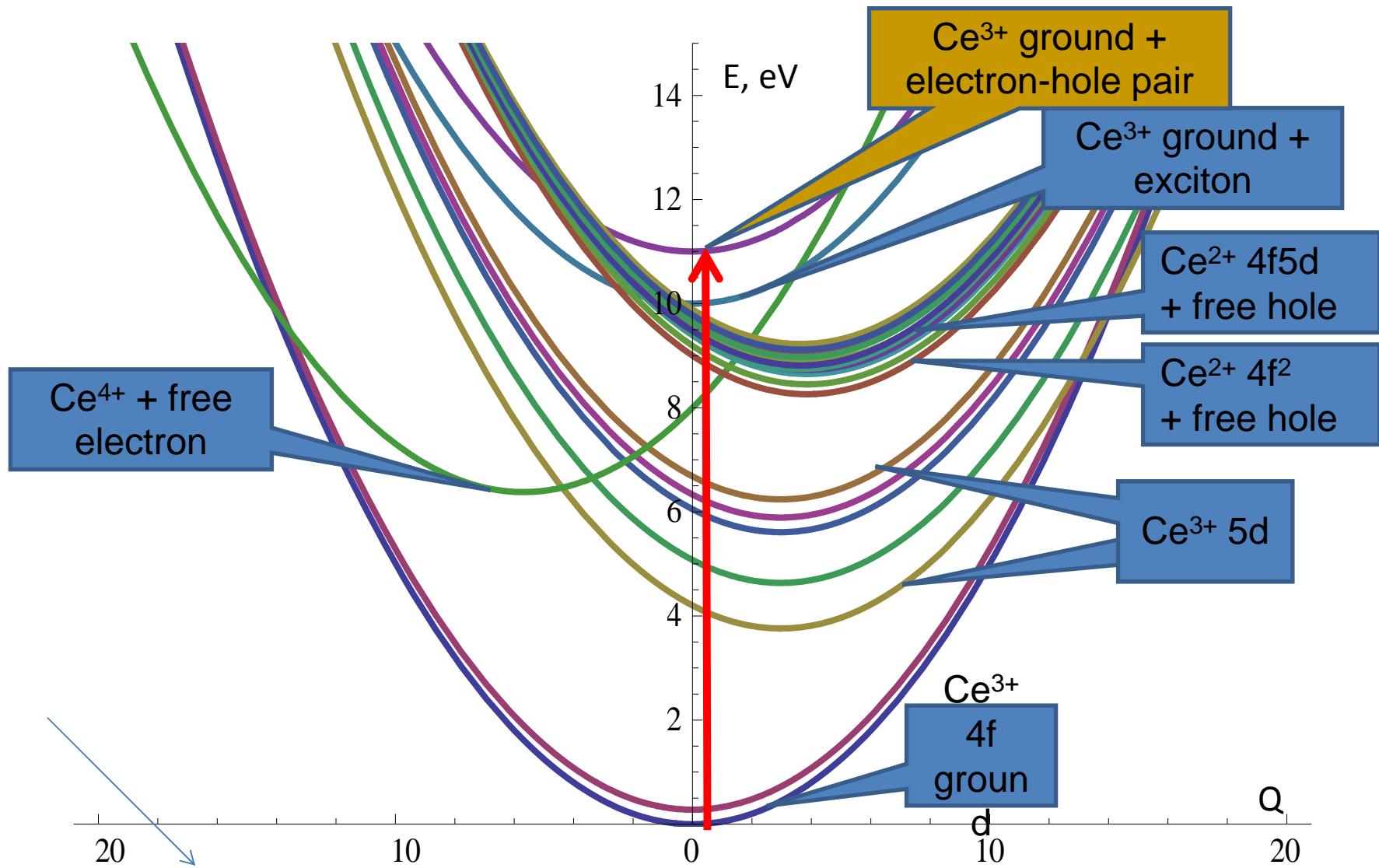
Excitation & ionization of Ce³⁺



Excitation & ionization of Ce^{3+}

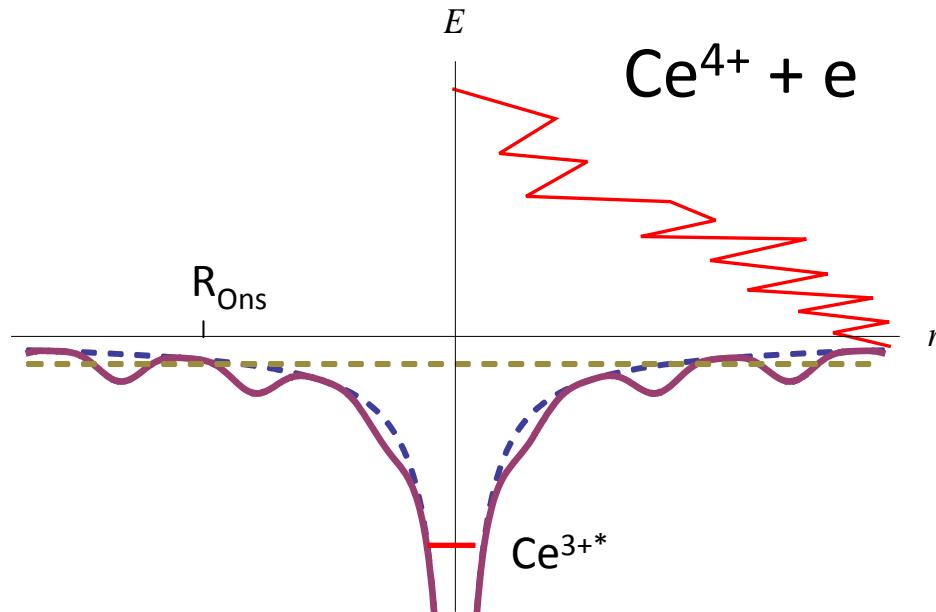


Excitation & ionization of Ce^{3+}

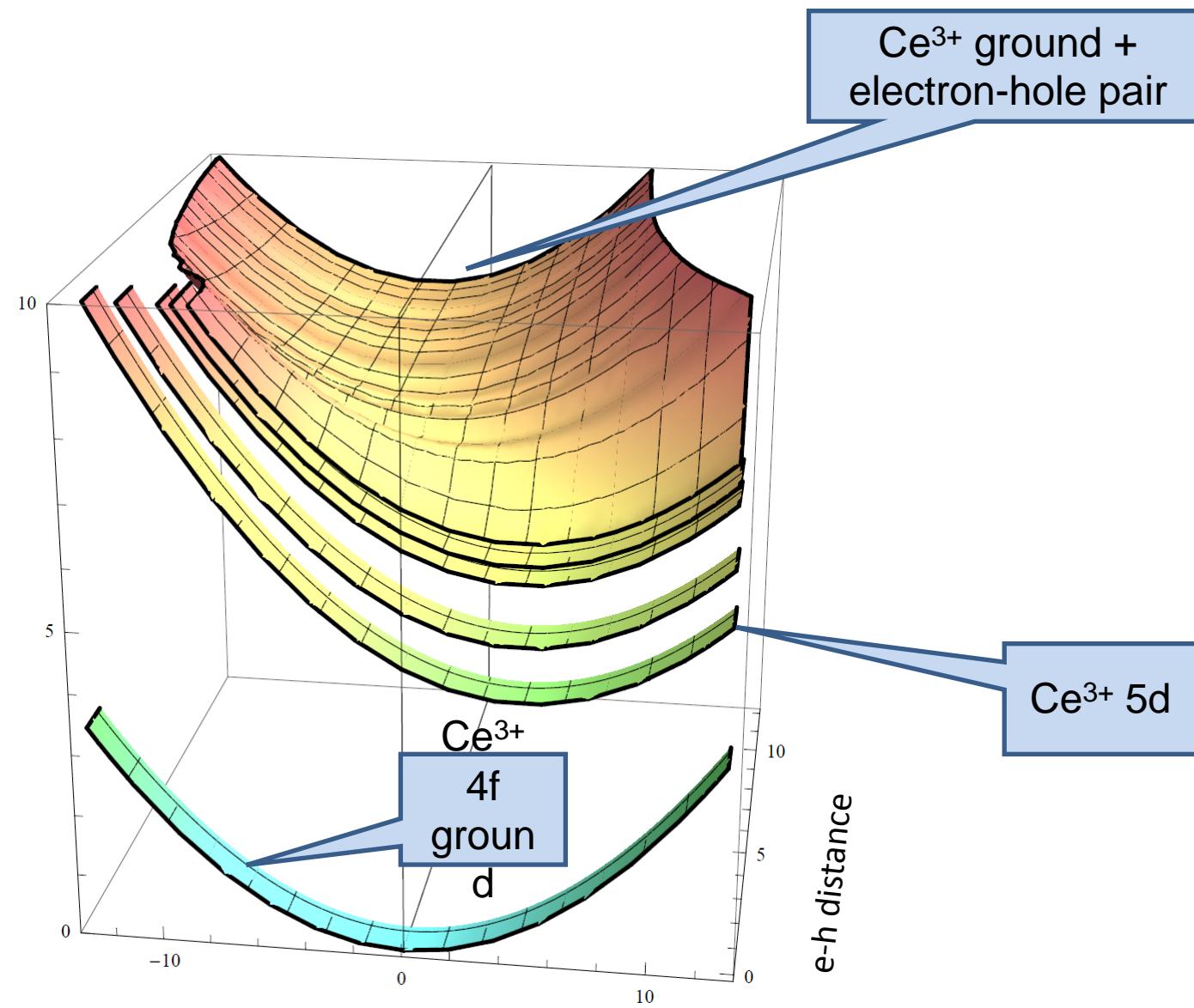


Ionization of Ce³⁺

Energy (eV)

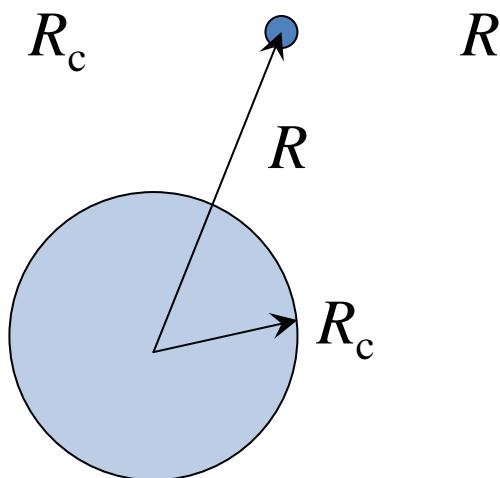
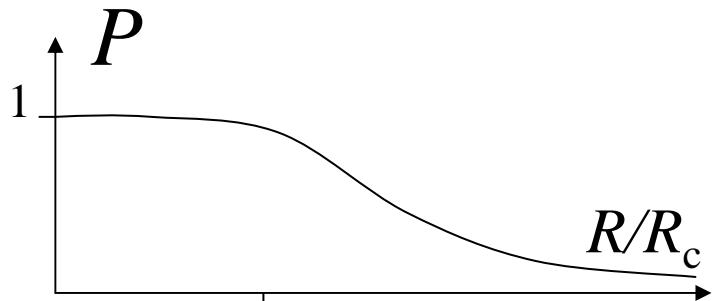


Excitation & ionization of Ce^{3+}



3D diffusion-controlled recombination

Recombination probability



3D

Black sphere

$$P = \begin{cases} 1, & r_{eh} < R_c \\ R_c/r_{eh}, & r_{eh} > R_c \end{cases}$$

Coulomb

$$P = 1 - \exp(-R_{Ons}/r_{eh})$$
$$\frac{e^2}{\varepsilon R_{Ons}} = k_B T$$

$$\varepsilon = 5.7$$

$$T = 300 \text{ K}$$

$$R_{Ons} = 10 \text{ nm}$$

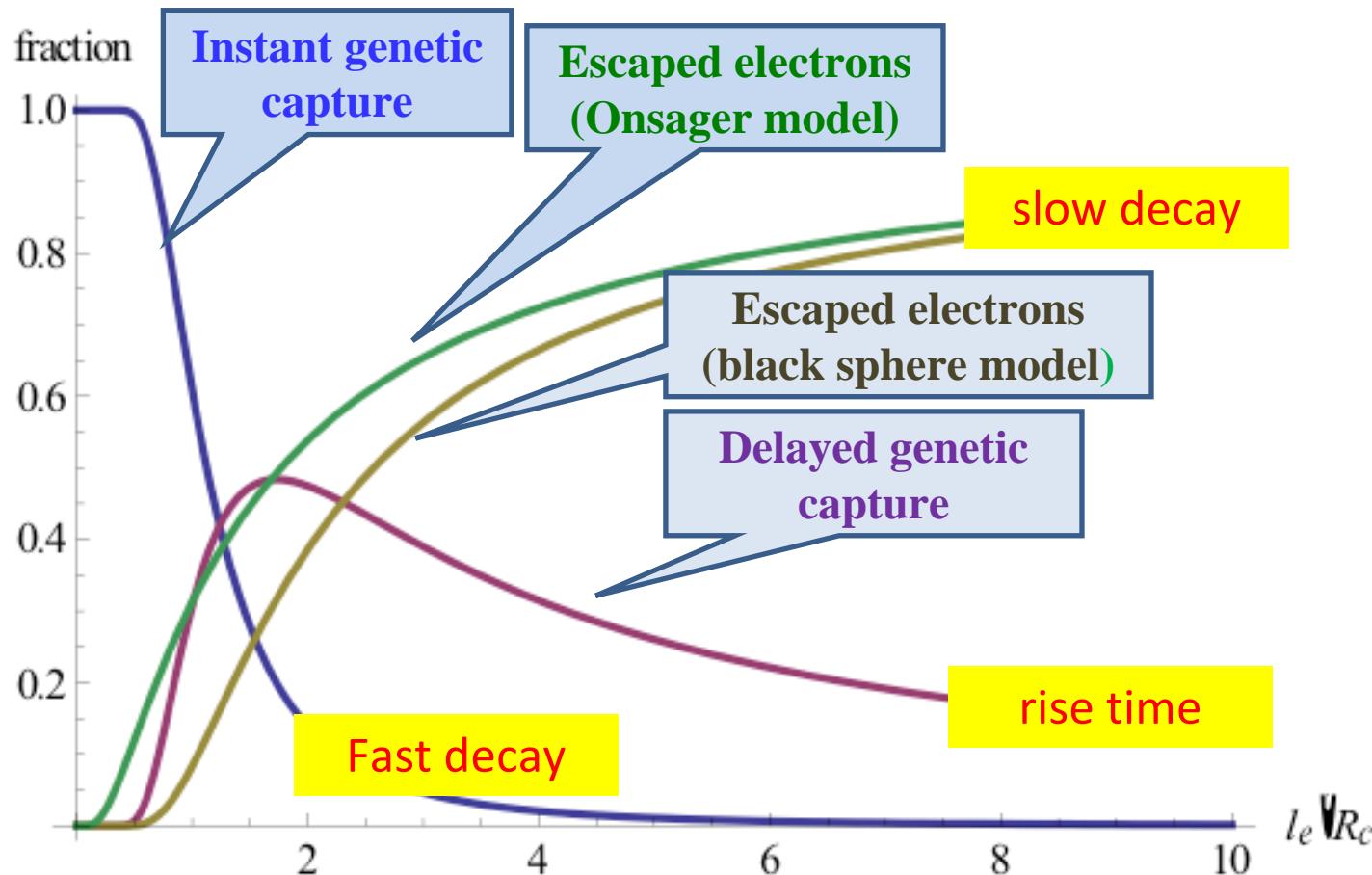
$$T = 77 \text{ K}$$

$$R_{Ons} = 38 \text{ nm}$$

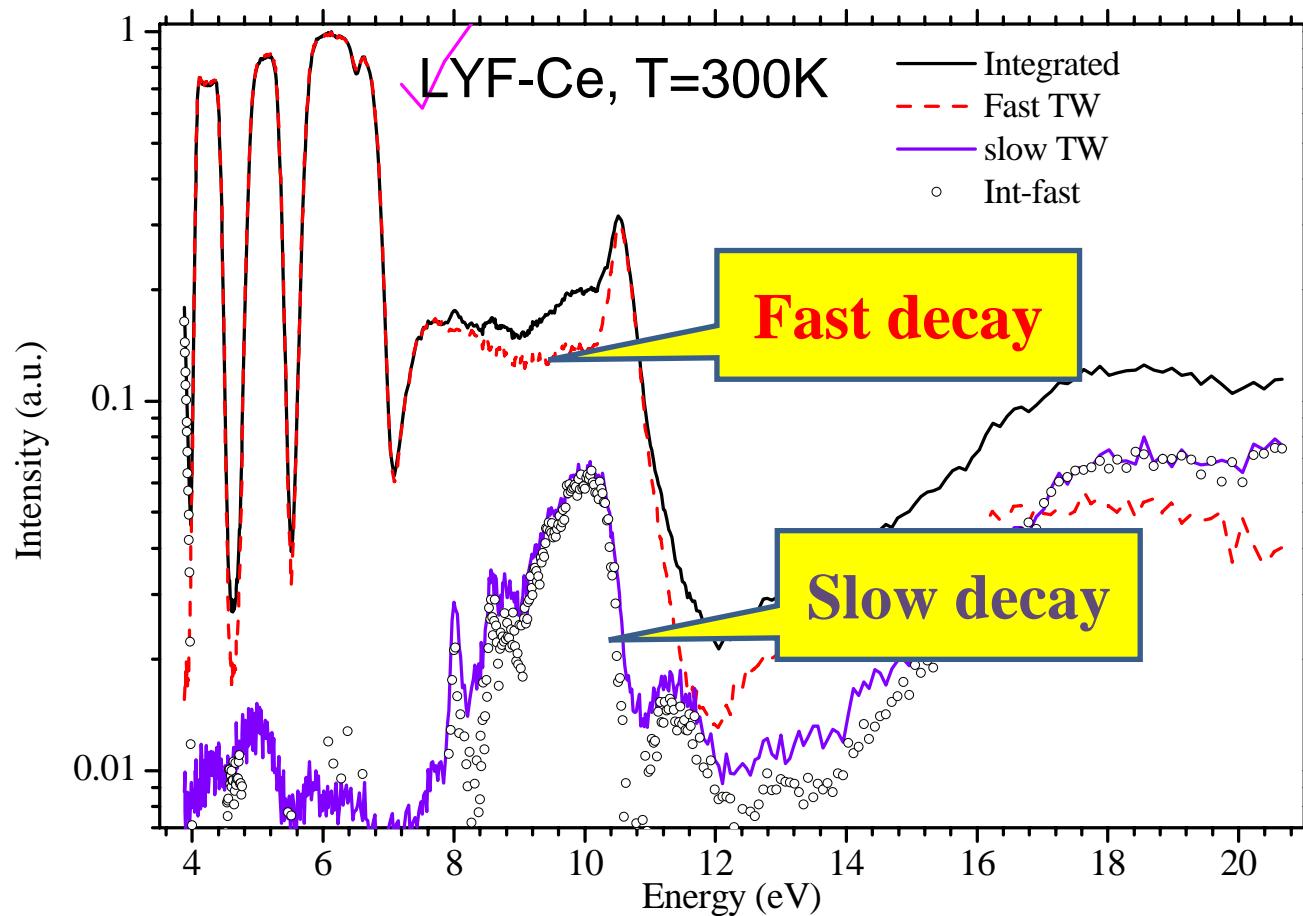
$$T = 10 \text{ K}$$

$$R_{Ons} = 300 \text{ nm } ???$$

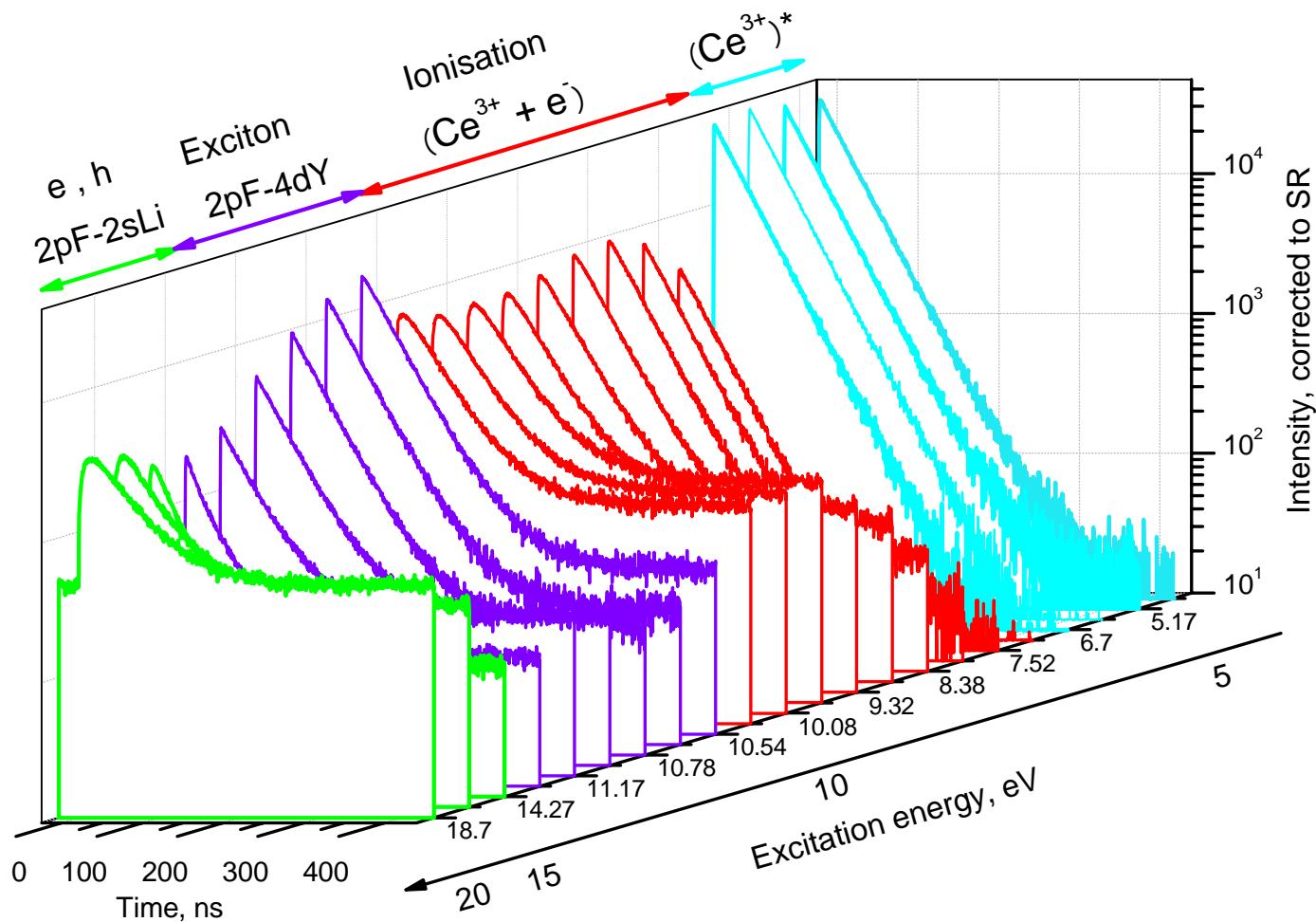
Recovery of Ce³⁺ centers after ionization



$\text{LiYF}_4:\text{Ce}^{3+}$ time resolved excitation spectra



$\text{LiYF}_4:\text{Ce}^{3+}$ decays, RT



Recovery of Ce³⁺ centers after ionization

$$\begin{aligned} -\left(\frac{d n_{Ce^{4+}}(t)}{dt}\right)_{diff} &= \boxed{\frac{N}{V} \left[\Phi\left(\frac{R_c}{R_0}\right) - \frac{2}{\sqrt{\pi}} \frac{R_c}{R_0} \exp\left(-\frac{R_c^2}{R_0^2}\right) + \frac{4}{3} \pi R_c^3 n_{nc} \right] \delta(t+0)} \\ &+ \frac{N}{V} \frac{4R_c^2 R_0 \sqrt{D} \exp\left(-\frac{R_c^2}{R_0^2}\right)}{\pi \sqrt{t} (R_0^2 + 4Dt)^2} + \frac{N}{V} \frac{4R_c D (R_0^2 + 4Dt - 2R_c^2)}{\sqrt{\pi} (R_0^2 + 4Dt)^{5/2}} \exp\left(-\frac{R_c^2}{R_0^2 + 4Dt}\right) \left[1 - \Phi\left(2 \frac{R_c}{R_0} \sqrt{\frac{Dt}{R_0^2 + 4Dt}}\right) \right] \\ &+ \boxed{4\pi D R_c n_{nc} \left(1 + \frac{R_c}{\sqrt{\pi Dt}}\right) n_{Ce^{4+}}(t)} \end{aligned}$$

3 main parameters:

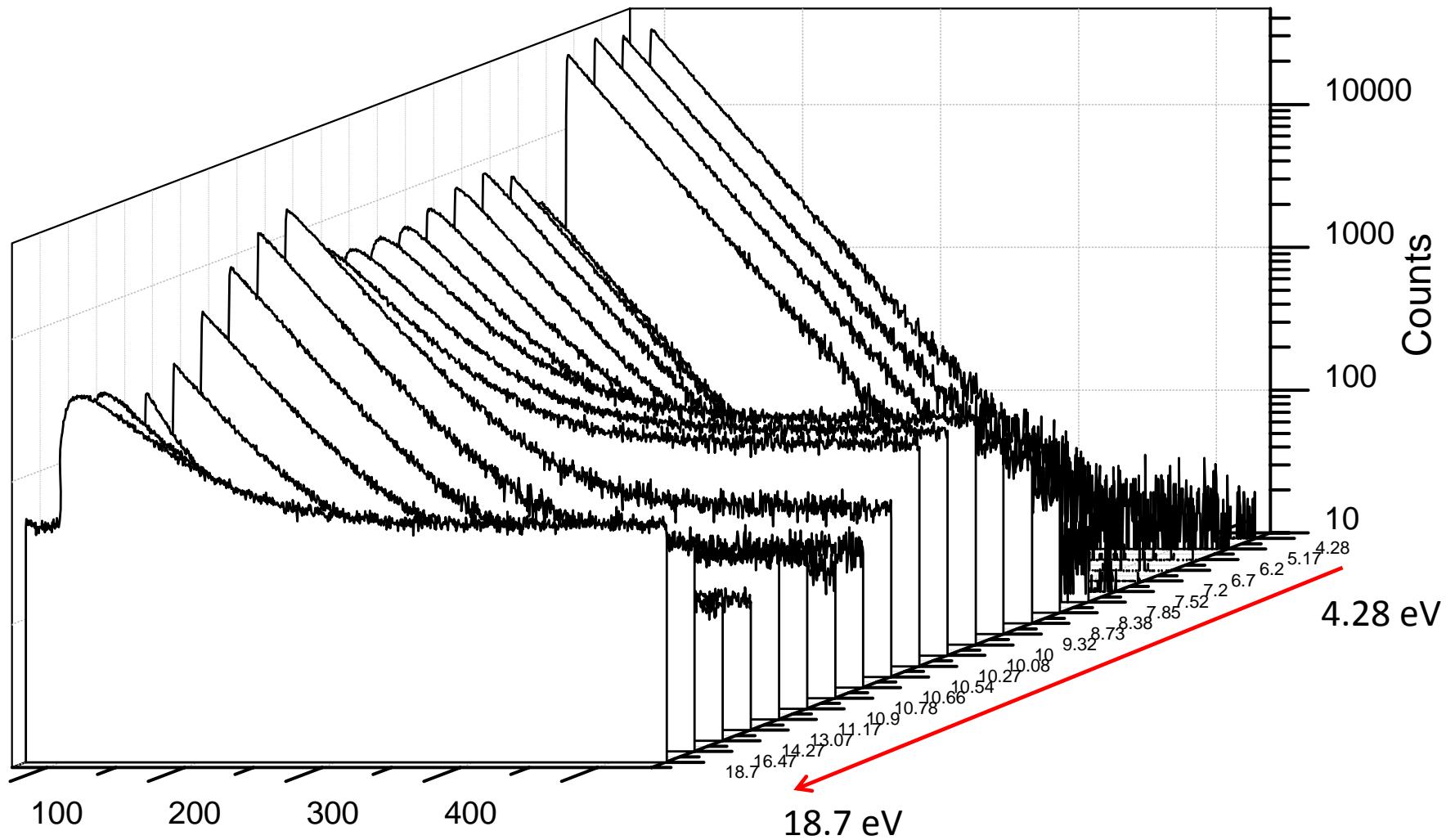
R_0/R_c (thermalization radius to capture radius)

n_{nc} (concentration of non-correlated carriers)

R_c^2/D (time of diffusion across capture sphere)

$\text{LiYF}_4:\text{Ce}^{3+}$ decays

K. Ivanovskikh, A. Belsky, M. Reid, Y. Guyot, L. Nurtdinova, V. Semashko, M.-F. Joubert,
to be published



$\text{LiYF}_4:\text{Ce}^{3+}$ 10 eV

4_28 5_17 6_2 6_7 7_2 7_52 7_85 8_38 8_73 9_32 10_08 10_27 10 10_54 10_66 10_78 10_9 11_17 13_07 14_27 16_47 18_7

trCe 28

qCe 0.0

trEx 0.1

qEx 0.0

xCe3Direct 0.0

a 1391.86

lev 25

s 26.2716

aDEx 0.0

kDEx 0.0

kDCe 0.0

R02Rc 2.89436

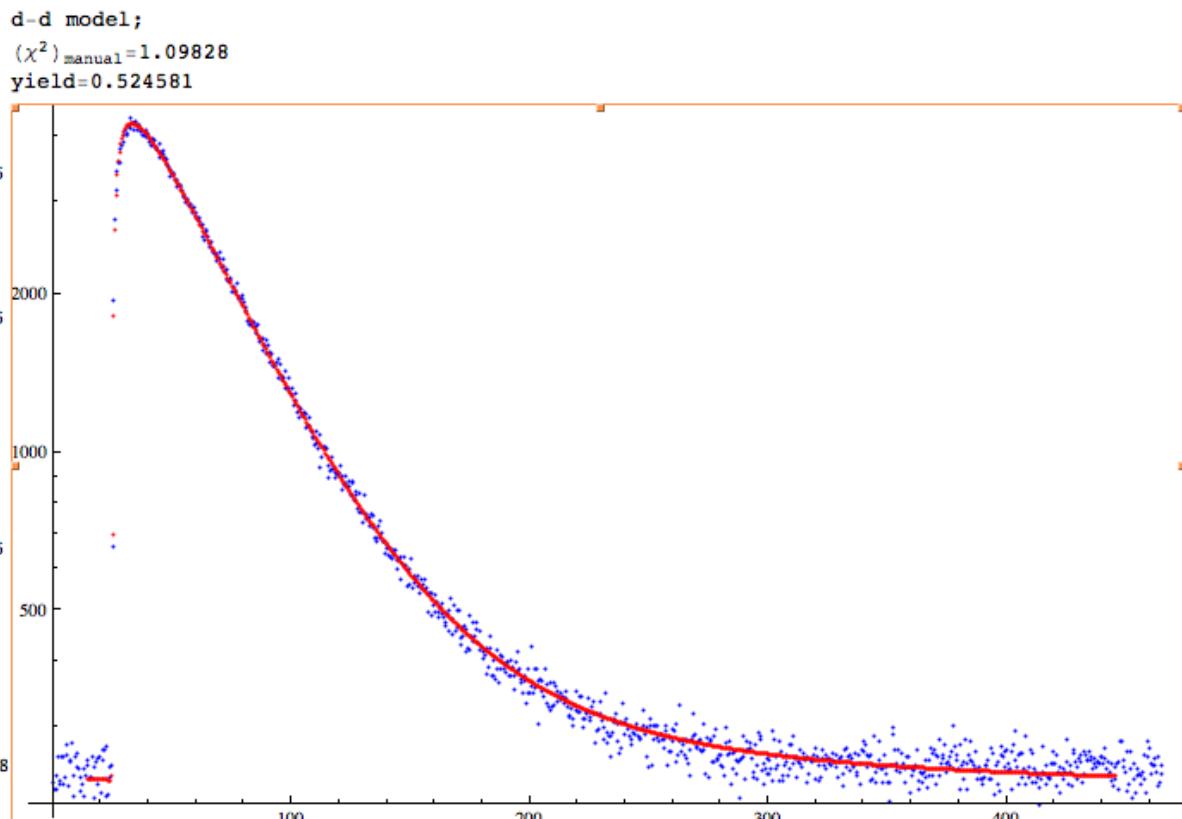
tDiffRc 1.0

frCe4 1.0

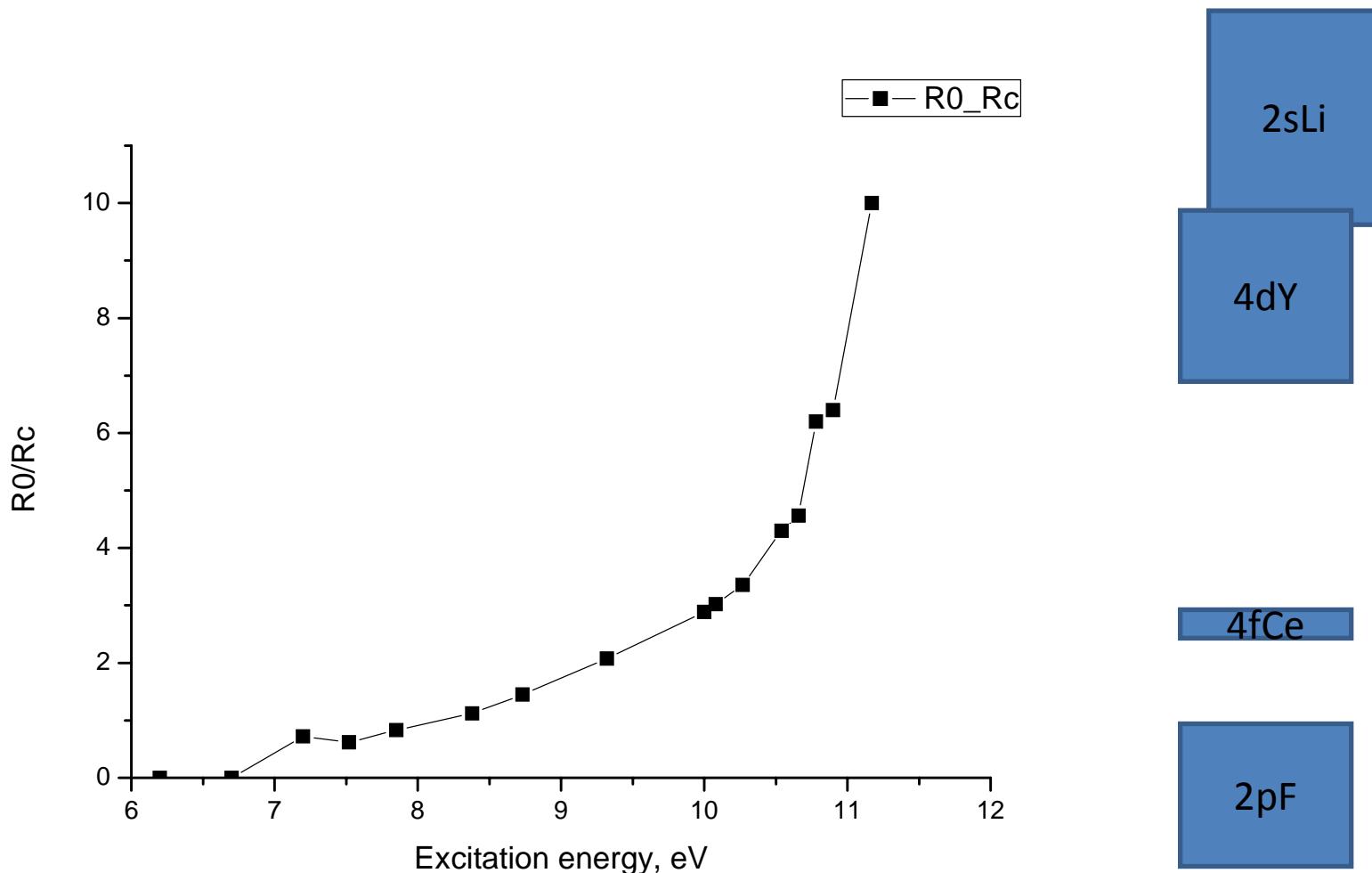
qnc 0.205608

beta02beta1 1.0

beta1 0.240466



$\text{LiYF}_4:\text{Ce}^{3+}$ R_0/R_c vs energy



Coupled processes of thermalization and spatial diffusion

Mean square of the thermalization distance

$$\langle r^2 \rangle_{E_{e0} \rightarrow E_e^{kin}} = 6 \int_{E_e^{kin}}^{E_{e0}} \frac{D^R(E')}{S(E')} dE'$$

Spatial distribution function

$$f(r, l_e(E_{e0})) = \frac{3\sqrt{6}r^2}{\sqrt{\pi}l_e^3(E_{e0})} \exp\left(-\frac{3r^2}{2l_e^2(E_{e0})}\right)$$

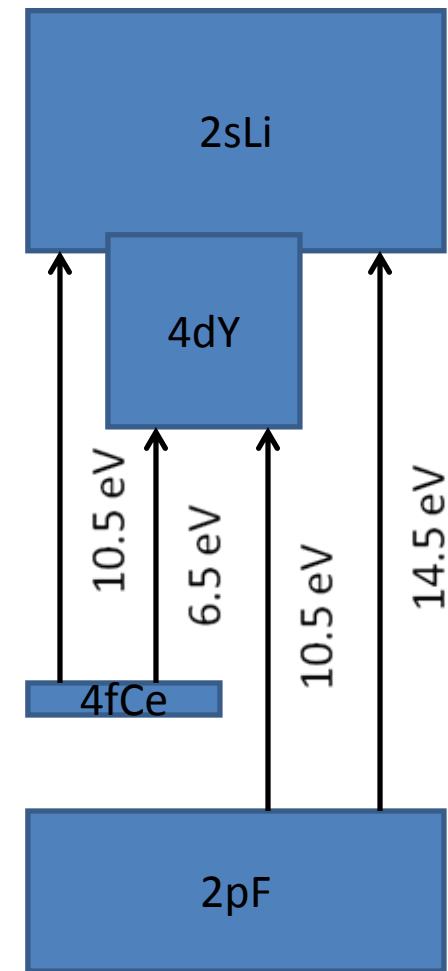
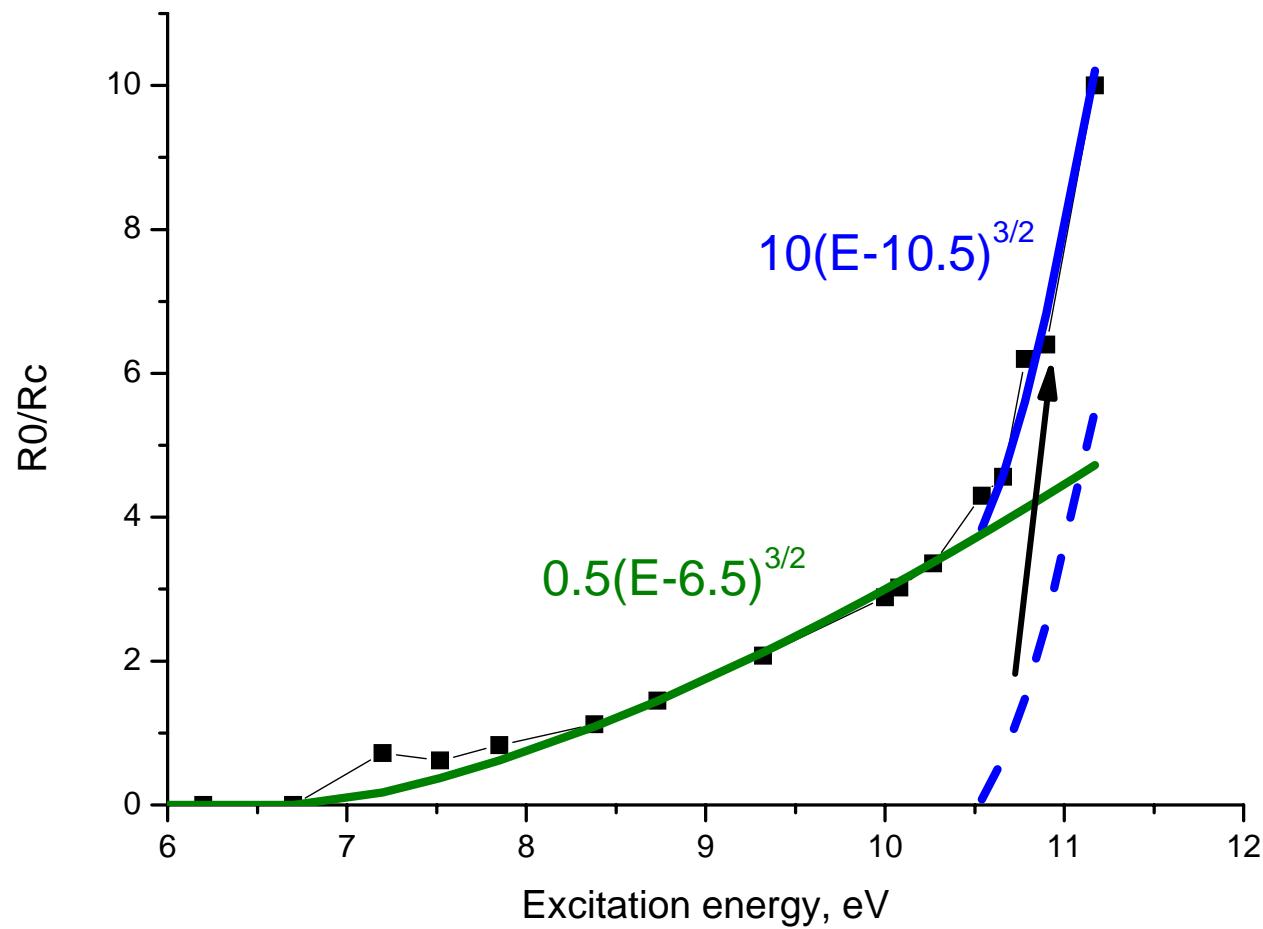
where thermalization length is

$$l_e(E_{e0}) = \sqrt{\langle r^2 \rangle_{E_{e0} \rightarrow k_B T}}$$

Thermalization length for one LO phonon branch

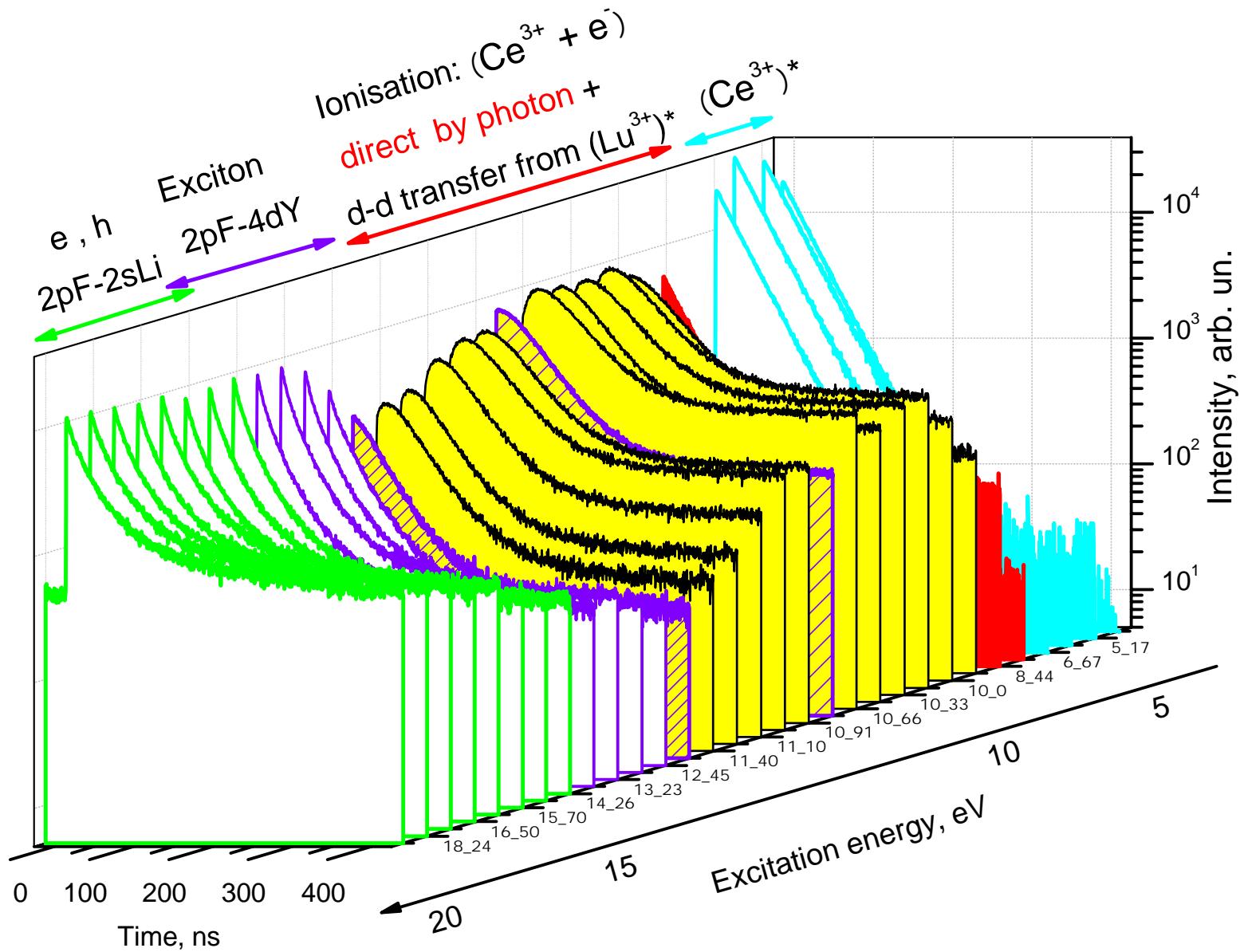
$$\begin{aligned} l_{e,LO}^2(E_{e0}) &= \frac{8}{3} a_B^2 \left(\frac{\tilde{\varepsilon}}{m_e^*/m_0} \right)^2 \tanh\left(\frac{\hbar\Omega_{LO}}{2k_B T} \right) \int_{\hbar\Omega_{LO}}^{E_{e0}} \left(\frac{E'}{\hbar\Omega_{LO}} \right)^2 \frac{1}{\ln(4E'/\hbar\Omega_{LO})} \frac{dE'}{\hbar\Omega_{LO}} \\ &= \frac{1}{24} a_B^2 \left(\frac{\tilde{\varepsilon}}{m_e^*/m_0} \right)^2 \tanh\left(\frac{\hbar\Omega_{LO}}{2k_B T} \right) \text{Ei}\left(3 \ln\left(\frac{4E_{e0}}{\hbar\Omega_{LO}} \right) \right), \end{aligned}$$

$\text{LiYF}_4:\text{Ce}^{3+}$ R_0/R_c vs energy



$$m_{\text{eff}, \text{4dY}}/m_{\text{eff}, \text{2sLi}} = 20$$

$\text{LiLuF}_4:\text{Ce}^{3+}$ decays, RT



LiLuF₄:Ce³⁺ 9.58 eV

4_27 | 5_17 | 6_2 | 6_67 | 7_36 | 8_44 | 9_58 | 10_0 | 10_16 | 10_33 | 10_51 | 10_66 | 10_83 | 10_91 | 10_97

11_10 | 11_23 | 11_40 | 12_02 | 12_45 | 12_92 | 13_23 | 13_67 | 14_26 | 14_94 | 15_70 | 16_32 | 16_50 | 17_06 | 18_24 | 19_02

trCe 28 [-+]

qCe 0 [-+]

trEx 80 [-+]

qEx 0 [-+]

xCe3Direct 0 [-+]

a 577.621 [-+]

lev 40 [-+]

s 33.47 [-+]

aDEX 8. [-+]

kDEX 0. [-+]

kDCe 0. [-+]

R02Rc 1.62 [-+]

tDiffRc 0.056 [-+]

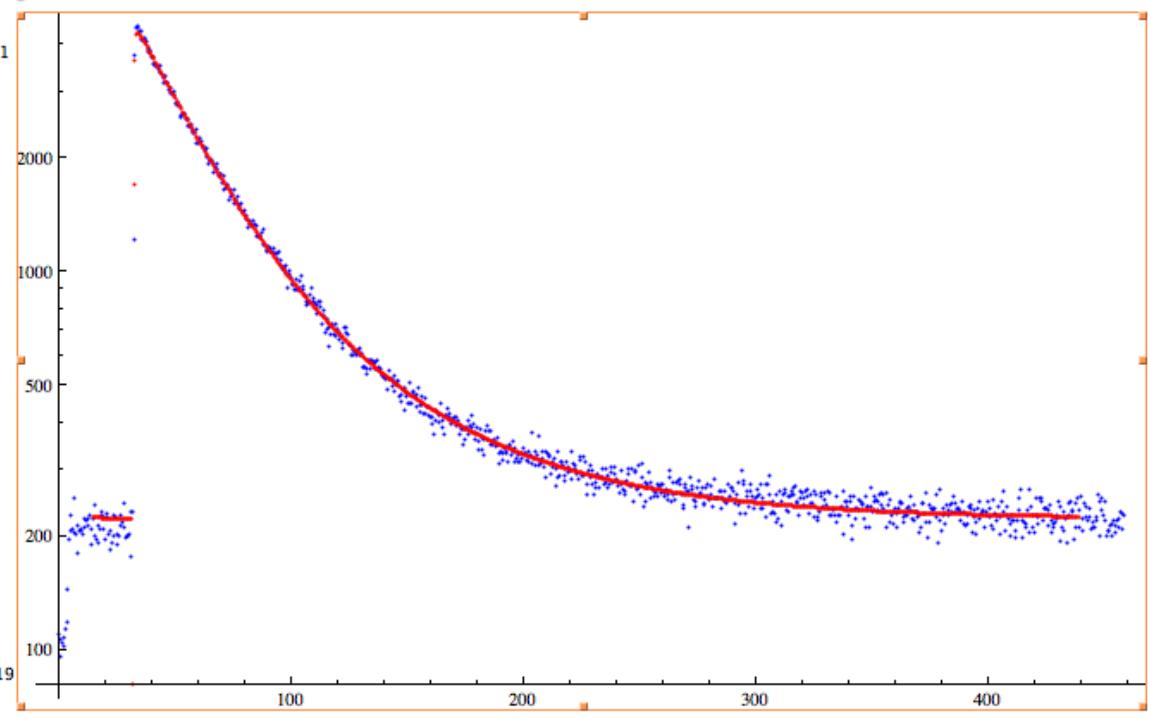
frCe4 1. [-+]

qnc 0.811719 [-+]

beta02beta1 0.454052 [-+]

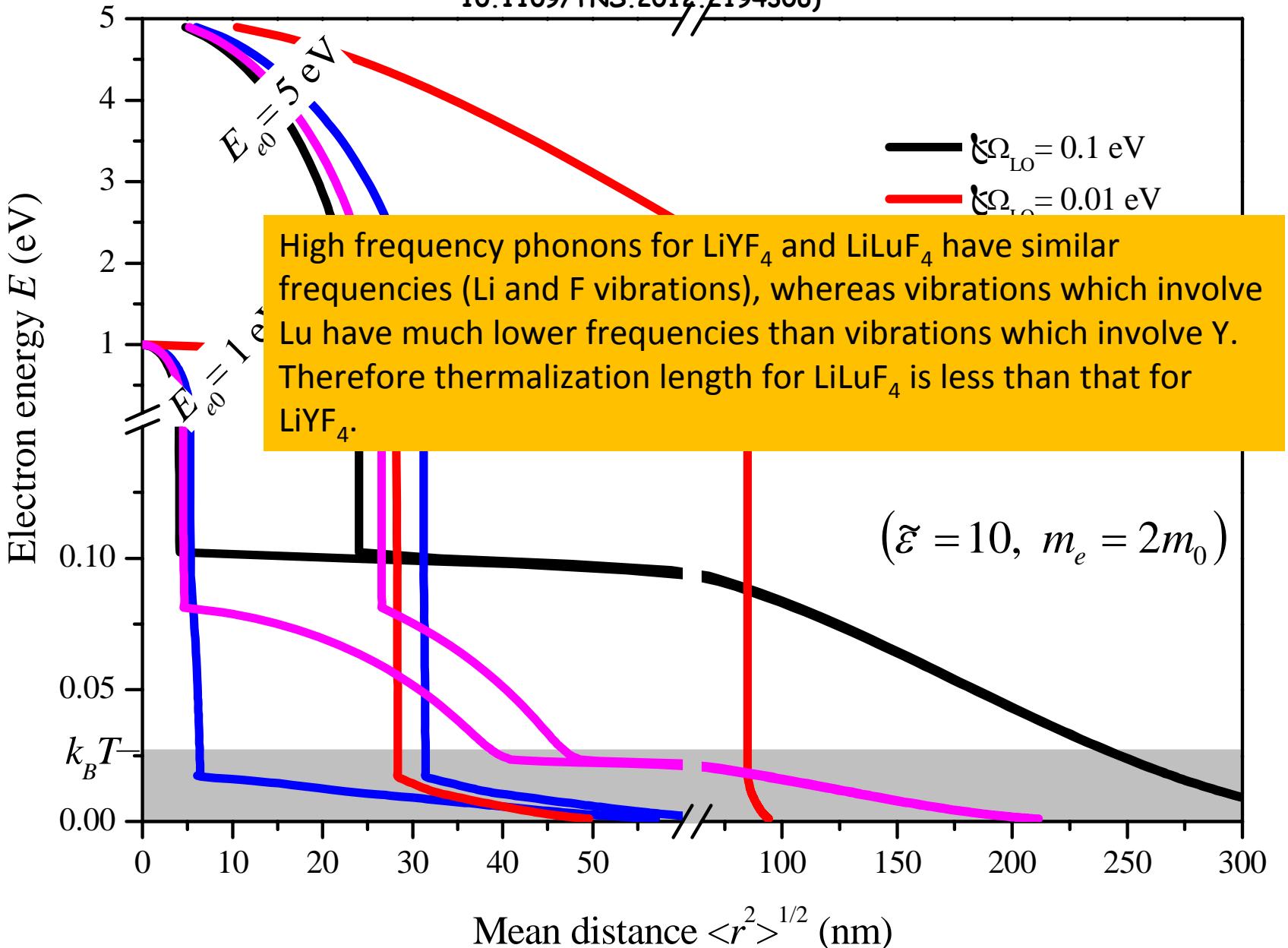
beta1 0.579436 [-+]

diff model;
 (χ^2) _{manual}=1.48518
yield=1.00294

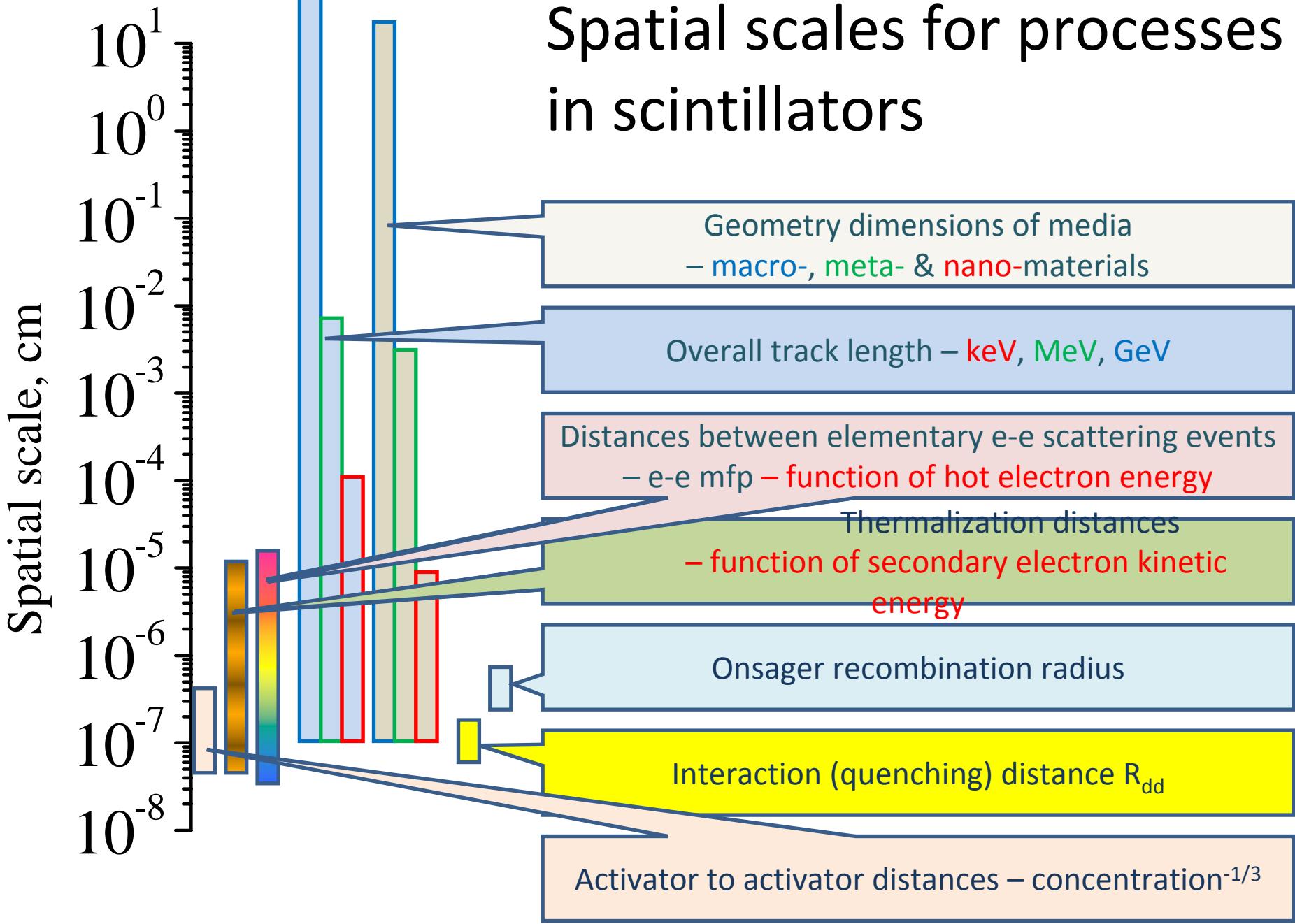


Estimation of mean thermalization distance R_0 for different initial kinetic energy energy

(R.Kirkin, V.Mikhailin, A.N.Vasil'ev, IEEE TNS, DOI
10.1109/TNS.2012.2194306)

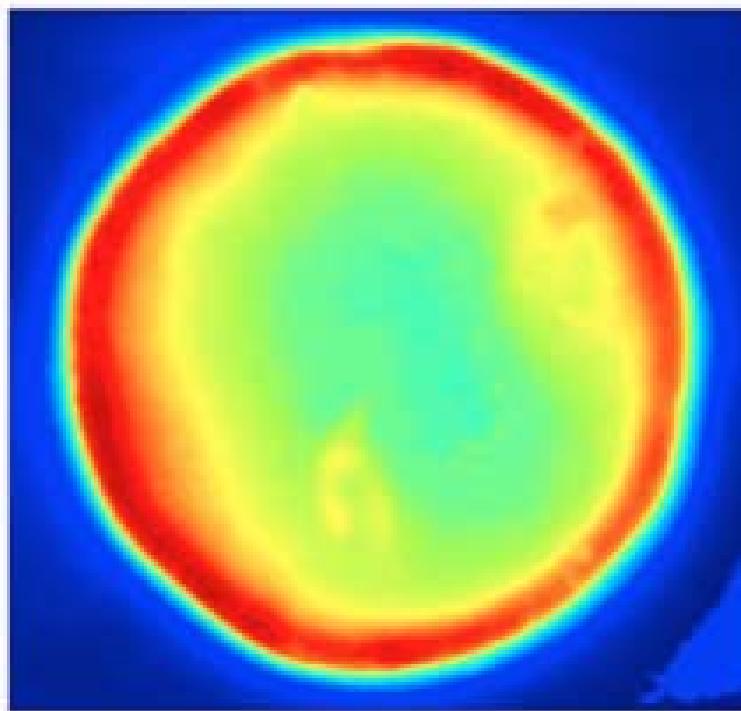


Spatial scales for processes in scintillators



Meta-scale

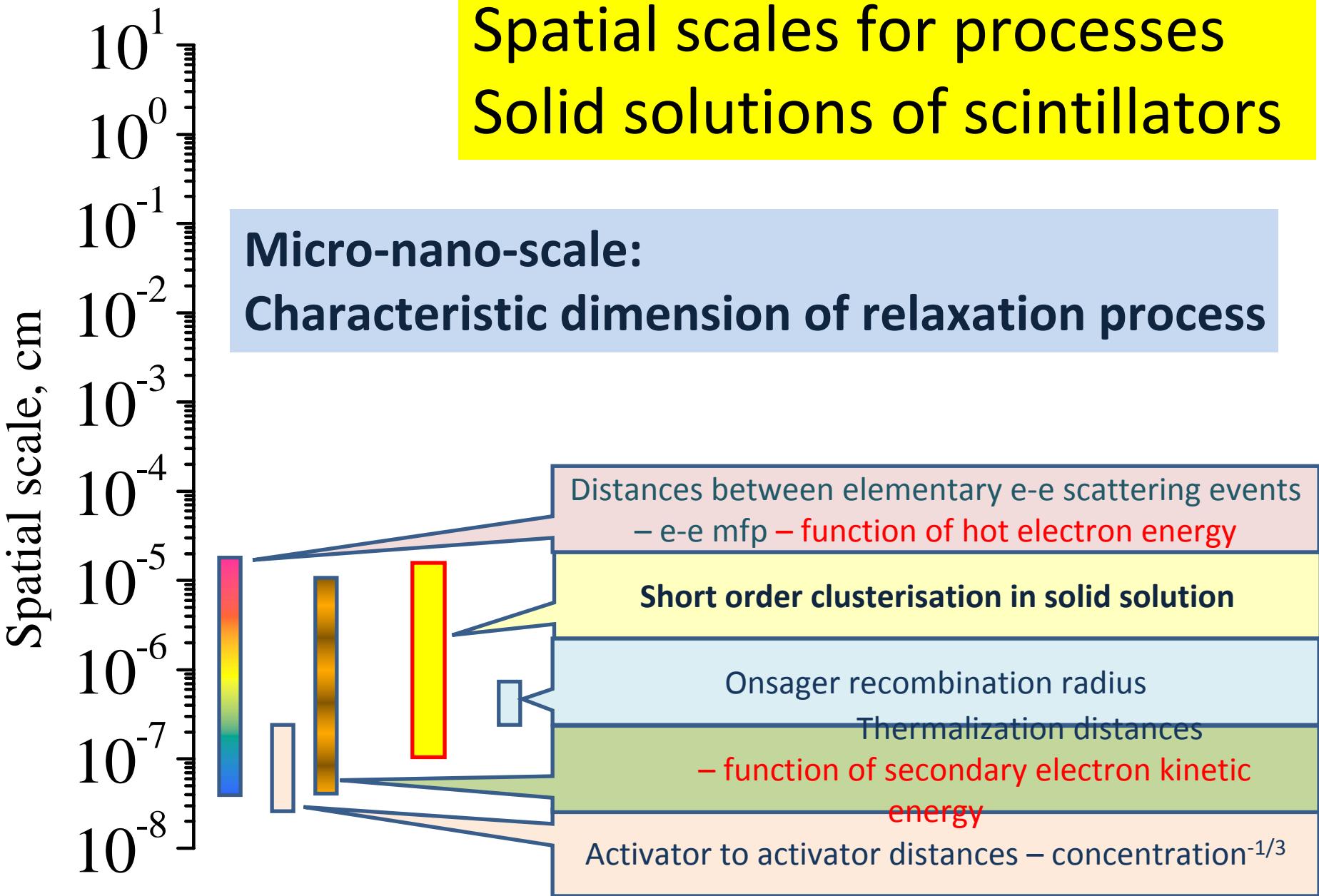
10 KeV electron excitation
of LuAG:Ce fiber d=1 mm



Non-uniform
distribution of
properties

understanding the relaxation in real materials

Spatial scales for processes Solid solutions of scintillators



Spatial scales for processes Solid solutions of scintillators

Micro-nano-scale: Modulation of crystal electronic structure

More evident reason is the modulation of band gap by variation of cations or anions ratio in solid solutions. It the case of very now $(\text{Zn}, \text{Cd})\text{S}$ solutions, and many others.

In this type of solid solution the suppression / creation of local states in forbidden energy gap is possible.

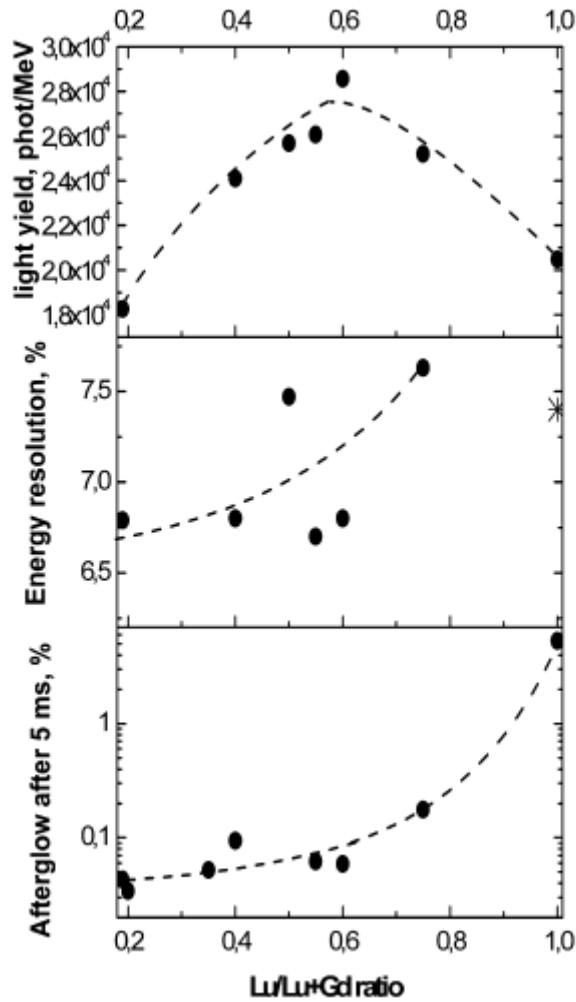
Spatial scales for processes Solid solutions of scintillators

Micro-nano-scale:

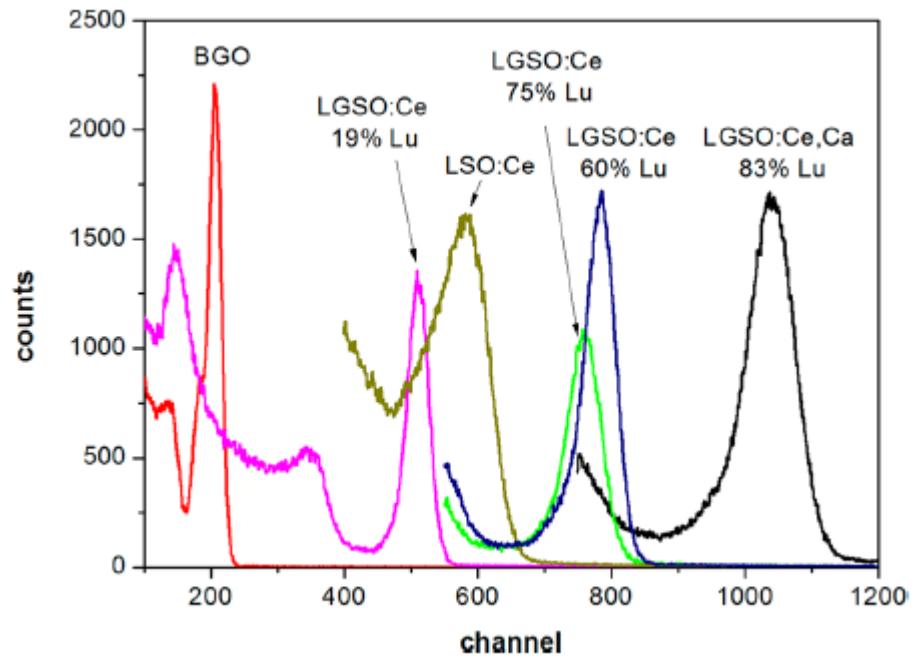
Short range separation of components of solid solutions

short-range separation in solid solution may lead to formation of potential barriers limiting the e & h diffusion length. Clusterization should modify not only the edges of conductance and valence bands. Phonon spectrum of the crystal and distribution of density of electronic states inside the bands may slow down hot carriers and

Ce-Doped (Lu,Gd)2SiO₅:Ce



Light yield (a), energy resolution (b) at 662 KeV, and afterglow (c) after 5 ms in LGSO:Ce crystals vs Lu concentration in host.



Pulse-height spectra of some LGSO:Ce and LGSO:Ce,Ca crystals in comparison with BGO and LSO:Ce

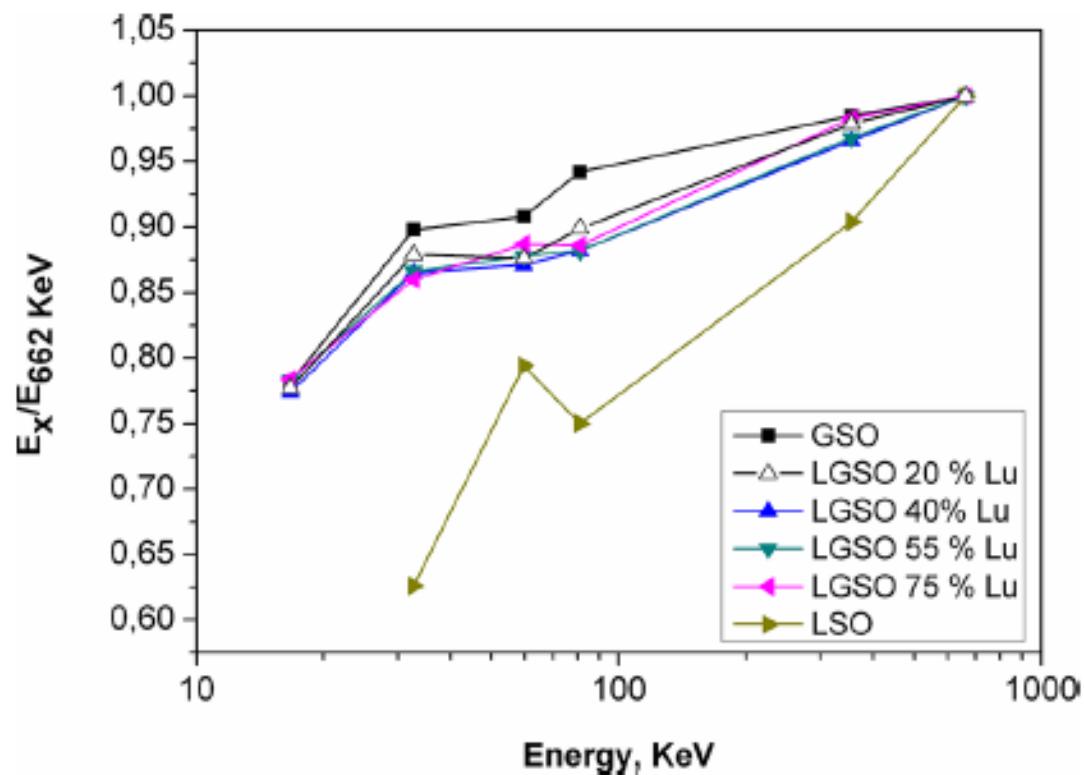


Figure 7. Nonproportionality characteristics of LGSO crystals with the different Lu contents.

Thank you for attention